L Number	Hits	Search Text	DB	Time stamp
1	2	4972251.pn.	USPAT;	2002/08/20 10:31
			EPO; JPO; DERWENT;	
2	528	(438/108).CCLS.	IBM_TDB USPAT;	2002/08/20 10:31
2	528	(430/100).CCLS.	US-PGPUB;	2002/06/20 10.31
			EPO; JPO;	
			DERWENT;	
2	2	///20/100\ GGTQ \	IBM_TDB	0000/00/00 10 00
3	3	((438/108).CCLS.) and protective with film with surface with (chip IC die	USPAT; US-PGPUB;	2002/08/20 10:33
	:	semiconductor)	EPO; JPO;	
			DERWENT;	
	001	(420/C) pala and much paties with film	IBM_TDB	2002/08/20 10:34
4	801	(438/\$).ccls. and protective with film with surface with (chip IC die	USPAT; US-PGPUB;	2002/08/20 10:34
		semiconductor)	EPO; JPO;	
			DERWENT;	
_	2.4	((438/\$).ccls. and protective with film	IBM_TDB	2002/08/20 11:29
5	34	with surface with (chip IC die	USPAT; US-PGPUB;	2002/08/20 11:29
		semiconductor)) and flip	EPO; JPO;	
			DERWENT;	
6	1256	(257/692).CCLS.	IBM_TDB USPAT;	2002/08/20 11:29
o l	1250	(2377 692). CCLS.	US-PGPUB;	2002/08/20 11.29
			EPO; JPO;	
			DERWENT;	
7	14	((257/692).CCLS.) and passivation and flip	IBM_TDB USPAT;	2002/08/20 11:30
'	14	((237,032).cols.) and passivation and flip	US-PGPUB;	2002/00/20 11.30
			EPO; JPO;	
			DERWENT;	
8	41	((257/692).CCLS.) and passivation	IBM_TDB USPAT;	2002/08/20 11:30
	3.1	((257, 052, 100H5.) una passivación	US-PGPUB;	2002,00,20 11.30
			EPO; JPO;	
			DERWENT; IBM TDB	
9	193	((257/692).CCLS.) and insulating with	USPAT;	2002/08/20 11:30
	•	layer	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
10	667	(257/\$).ccls. and passivation and flip	USPAT;	2002/08/20 11:31
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
11	249	1 ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2002/08/20 11:31
		and passivation with pad	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2682	Continuation with PCT	USPAT;	2002/08/19 12:03
			US-PGPUB; EPO; JPO;	
			DERWENT;	ا ہے ا
			IBM_TDB	
_	18	(Continuation with PCT) and Continuation with PCT and (257/\$).ccls.	USPAT; US-PGPUB;	2002/08/19 12:16
		with FOI and (237/9).COIS.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/08/19 14:55
_	2	5470787.pn.	USPAT; US-PGPUB;	2002/00/19 14:55
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

Page 1

_3,	

_	472	(passivation with layer with made) and (438/\$).ccls.	USPAT; US-PGPUB; EPO; JPO;	2002/08/19 14:57
}			DERWENT;	
-	50	((passivation with layer with made) and (438/\$).ccls.) and solder with bump	IBM_TDB USPAT; US-PGPUB;	2002/08/19 15:07
			EPO; JPO; DERWENT; IBM_TDB	0000/00/10 14 50
_	40 521	5736456.URPN. passivation with layer with (silicon adj nitride silicon oxide MgO) and bump	USPAT USPAT; US-PGPUB; EPO; JPO;	2002/08/19 14:59 2002/08/19 15:14
	222	(passivation with layer with (silicon adj	DERWENT; IBM_TDB USPAT;	2002/08/19 15:15
	222	nitride silicon oxide MgO) and bump) and (257/\$).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/00/15 13:15
_	252	passivation with layer with (silicon adj nitride silicon adj oxide MgO) and bump	USPĀT; US-PGPUB; EPO; JPO;	2002/08/19 15:15
_	109	(passivation with layer with (silicon adj nitride silicon adj oxide MgO) and bump) and (257/\$).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 15:25
-	5	("4434434" "5268072" "5629564" "5785236" "5795819").PN.	IBM_TDB USPAT	2002/08/19 15:21
_	90	passivation with layer with thermal with expansion	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 15:44
-	22218	silicon with germanium dioxide with layer with thermal with coefficient	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 15:52
_	151	(silicon with germanium dioxide with layer with thermal with coefficient) and passivation with layer and bump	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 15:50
_	3	silicon with germanium with dioxide with layer with thermal with coefficient	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/19 15:53
	479795	silicon with dioxide with coefficient with thermal expansion	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/19 15:57
_	9020	(silicon with dioxide with coefficient with thermal expansion) and (257/\$).ccls.	DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/19 15:58
_	1751	((silicon with dioxide with coefficient with thermal expansion) and (257/\$).ccls.) and bump	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 15:56
			IBM_TDB	l

_	325	(((silicon with dioxide with	USPAT;	2002/08/19 15:56
		coefficient with thermal expansion) and	US-PGPUB;	
		(257/\$).ccls.) and bump) and passivation	EPO; JPO;	
		-	DERWENT;	
			IBM TDB	
_	243	(((silicon with dioxide with	USPAT;	2002/08/19 15:56
		coefficient with thermal expansion) and	EPO; JPO;	
		(257/\$).ccls.) and bump) and passivation	DERWENT;	
			IBM_TDB	
_	277	silicon with dioxide with coefficient	USPAT;	2002/08/19 16:03
		with thermal with expansion	EPO; JPO;	
		_	DERWENT;	
			IBM TDB	
i –	72	(silicon with dioxide with coefficient	USPAT;	2002/08/19 16:00
		with thermal with expansion) and	US-PGPUB;	
		(257/\$).ccls.	EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
_	0	silicon adj dioxide with "coefficient of	USPAT;	2002/08/19 16:04
		thermal expansion"	EPO; JPO;	
		_	DERWENT;	
			IBM_TDB	İ
_	116	silicon adj dioxide with "thermal	USPAT;	2002/08/19 16:13
1		expansion coefficient"	EPO; JPO;	
		_	DERWENT;	
			IBM_TDB	
_	20673	silicon with germanium dioxide with	USPAT;	2002/08/19 16:14
		"thermal expansion coefficient"	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3		USPAT;	2002/08/19 16:21
		"thermal expansion coefficient"	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7	102220011 112011 112011 112011 112011	USPAT;	2002/08/19 16:27
		"thermal expansion"	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	4		USPAT;	2002/08/19 16:22
ļ		"thermal expansion") not (silicon with	EPO; JPO;	
		germanium with dioxide with "thermal	DERWENT;	
		expansion coefficient")	IBM_TDB	
-	9		USPAT;	2002/08/20 09:42
		"thermal expansion"	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	1		US-PGPUB	2002/08/19 16:31
1		"thermal expansion"		